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Harry J. Levinson

Mircea V. Dusa

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Contents

Part One

xvii	Symposium Committees
xix	Conference Committee

SESSION 1 INVITED SESSION

- 7274 02 **Alternative optical technologies: more than curiosities? (Keynote Paper)** [7274-01]
B. W. Smith, Rochester Institute of Technology (United States)

SESSION 2 RESOLUTION ENHANCEMENT

- 7274 04 **Overcoming the challenges of 22-nm node patterning through litho-design co-optimization** [7274-03]
M. Burkhardt, J. C. Arnold, IBM Research (United States); Z. Baum, IBM SRDC (United States); S. Burns, J. Chang, J. Chen, IBM Research (United States); J. Cho, V. Dai, Y. Deng, Advanced Micro Devices, Inc. (United States); S. Halle, G. Han, S. Holmes, D. Horak, IBM SRDC (United States); S. Kanakasabapathy, IBM Research (United States); R. H. Kim, Advanced Micro Devices, Inc. (United States); A. Klatchko, Freescale Corp. (United States); C. S. Koay, A. Krasnoperova, IBM SRDC (United States); Y. Ma, Advanced Micro Devices, Inc. (United States); E. McLellan, K. Petrillo, S. Schmitz, IBM SRDC (United States); C. Tabery, Advanced Micro Devices, Inc. (United States); Y. Yin, L. Zhuang, IBM SRDC (United States); Y. Zou, J. Kye, Advanced Micro Devices, Inc. (United States); V. Paruchuri, IBM Research (United States); S. Mansfield, IBM SRDC (United States); C. Spence, Advanced Micro Devices, Inc. (United States); M. Colburn, IBM Research (United States)
- 7274 05 **Improved model predictability by machine data in computational lithography and application to laser bandwidth tuning** [7274-04]
S. Hunsche, Q. Zhao, X. Xie, Brion Technologies Inc., ASML (United States); R. Socha, ASML (United States); H.-Y. Liu, Brion Technologies (United States); P. Nikolsky, A. Ngai, P. van Adrichem, ASML Netherlands B.V. (Netherlands); M. Crouse, ASML Corp. (United States); I. Lalovic, Cymer, Inc. (United States)
- 7274 07 **Contact mask optimization and SRAF design** [7274-06]
U. P. Schroeder, Infineon Technologies (United States) and IBM Semiconductor Research and Development Ctr. (USA); C. Tabery, Advanced Micro Devices Inc. (United States) and IBM Semiconductor Research and Development Ctr. (USA); B. Morgenfeld, IBM (United States) and IBM Semiconductor Research and Development Ctr. (USA); H. Kanai, Toshiba Corp. (United States) and IBM Semiconductor Research and Development Ctr. (USA)

SESSION 3 SOURCE AND MASK OPTIMIZATION

- 7274 08 **A study of source and mask optimization for ArF scanners** [7274-07]
T. Matsuyama, T. Nakashima, T. Noda, Nikon Corp. (Japan)
- 7274 09 **Intensive optimization of masks and sources for 22nm lithography** [7274-08]
A. E. Rosenbluth, D. O. Melville, IBM Thomas J. Watson Research Ctr. (United States); K. Tian, S. Bagheri, J. Tirapu-Azpiroz, K. Lai, IBM Semiconductor Research and Development Ctr. (United States); A. Waechter, IBM Thomas J. Watson Research Ctr. (United States); T. Inoue, IBM Tokyo Research Lab. (Japan); L. Ladanyi, F. Barahona, K. Scheinberg, IBM Thomas J. Watson Research Ctr. (United States); M. Sakamoto, H. Muta, IBM Tokyo Research Lab. (Japan); E. Gallagher, T. Faure, M. Hibbs, IBM Systems and Technology Group (United States); A. Tritchkov, Y. Granik, Mentor Graphics Corp. (United States)
- 7274 0A **Experimental result and simulation analysis for the use of pixelated illumination from source mask optimization for 22nm logic lithography process** [7274-09]
K. Lai, IBM Microelectronics (United States); A. E. Rosenbluth, IBM Yorktown Research Ctr. (United States); S. Bagheri, IBM Microelectronics (United States); J. Hoffnagle, IBM Almaden Research Ctr. (United States); K. Tian, IBM Microelectronics (United States); D. Melville, IBM Yorktown Research Ctr. (United States); J. Tirapu-Azpiroz, IBM Microelectronics (United States); M. Fakhry, Mentor Graphics Corp. (United States); Y. Kim, IBM Almaden Research Ctr. (United States); S. Halle, G. McIntyre, IBM Microelectronics (United States); A. Wagner, IBM Yorktown Research Ctr. (United States); G. Burr, IBM Almaden Research Ctr. (United States); M. Burkhardt, IBM Yorktown Research Ctr. (United States); D. Corliss, IBM Microelectronics (United States); E. Gallagher, T. Faure, M. Hibbs, IBM Mask House (United States); D. Flagello, ASML US, Inc. (United States); J. Zimmermann, B. Kneer, F. Rohmund, F. Hartung, C. Hennerkes, M. Maul, Carl Zeiss SMT AG (Germany); R. Kazinczi, A. Engelen, R. Carpaij, R. Groenendijk, J. Hageman, ASML (Netherlands); C. Russ, Formerly Carl Zeiss SMT AG (Germany)
- 7274 0B **Enabling process window improvement at 45nm and 32nm with free-form DOE illumination** [7274-10]
T. H. Coskun, A. Sezginer, V. Kamat, M. Kruger, B. Yenikaya, Cadence Design Systems, Inc. (United States); J. Carriere, J. Stack, M. Himel, Tessera (United States)

- 7274 0C **Benefits and trade-offs of global source optimization in optical lithography** [7274-11]
K. Tian, A. Krasnoperova, IBM Semiconductor Research and Development Ctr. (United States); D. Melville, A. E. Rosenbluth, D. Gil, IBM Thomas J. Watson Research Ctr. (United States); J. Tirapu-Azpiroz, K. Lai, S. Bagheri, C. Chen, B. Morgenfeld, IBM Semiconductor Research and Development Ctr. (United States)

SESSION 4 SPACER-BASED PROCESSES

- 7274 0D **Demonstration of 32nm half-pitch electrical testable NAND FLASH patterns using self-aligned double patterning** [7274-149]
S. Sun, C. Bencher, Y. Chen, H. Dai, M. Cai, J. Jin, P. Blanco, L. Miao, P. Xu, X. Xu, J. Yu, R. Hung, S. Oemardani, O. Chan, C.-P. Chang, C. Ngai, Applied Materials, Inc. (United States)

7274 0E	Advanced self-aligned double patterning development for sub-30-nm DRAM manufacturing [7274-12] W. Shiu, H. J. Liu, J. S. Wu, T.-L. Tseng, C. T. Liao, C. M. Liao, J. Liu, T. Wang, Nanya Technology Corp. (Taiwan)
7274 0F	Process step reduction at negative tone spacer patterning technique using developer soluble bottom ARC [7274-13] W.-Y. Jung, J.-D. Eom, S.-M. Jeon, J.-H. Lee, B.-S. Lee, J.-W. Kim, Hynix Semiconductor, Inc. (Korea, Republic of)
7274 0G	Gridded design rule scaling: taking the CPU toward the 16nm node [7274-14] C. Bencher, H. Dai, Y. Chen, Applied Materials, Inc. (United States)

SESSION 5 DOUBLE PATTERNING I

7274 0H	Split, overlap/stitching, and process design for double patterning considering local reflectivity variation by using rigorous 3D wafer-topography/lithography simulation [7274-16] I. Kamohara, Synopsys Japan (Japan); T. Schmoeller, Synopsys GmbH (Germany)
7274 0I	Advances and challenges in dual-tone development process optimization [7274-17] C. Fonseca, M. Somervell, S. Scheer, W. Printz, Tokyo Electron America, Inc. (United States); K. Nafus, S. Hatakeyama, Y. Kuwahara, T. Niwa, Tokyo Electron Kyushu, Ltd. (Japan); S. Bernard, R. Gronheid, IMEC (Belgium)
7274 0J	New process proximity correction using neural network in spacer patterning technology [7274-18] F. Nakajima, T. Kotani, S. Tanaka, M. Asano, S. Inoue, Toshiba Corp. Semiconductor Co. (Japan)
7274 0K	32nm and below logic patterning using optimized illumination and double patterning [7274-19] M. C. Smayling, Tela Innovations, Inc. (United States); V. Axelrad, Sequoia Design Systems, Inc. (United States)

SESSION 6 DOUBLE PATTERNING II

7274 0M	Analysis of topography effects on lithographic performance in double patterning applications [7274-21] J. Siebert, Synopsys, Inc. (Germany); P. Brooker, Synopsys, Inc. (United States); T. Schmoeller, T. Klimpel, Synopsys, Inc. (Germany)
7274 0N	Ultimate contact hole resolution using immersion lithography with line/space imaging [7274-23] V. Truffert, J. Bekaert, F. Lazzarino, M. Maenhoudt, A. Miller, M. Moelants, IMEC vzw (Belgium); T. Wu, IMEC vzw (Belgium) and TSMC, Ltd. (Taiwan)
7274 0O	Efficient simulation and optimization of wafer topographies in double patterning [7274-24] F. Shao, P. Evanschitzky, T. Fühner, A. Erdmann, Fraunhofer Institute of Integrated Systems

and Device Technology (Germany)
7274 OP **Investigating the impact of topography on pitch splitting double patterning using rigorous physical simulation** [7274-22]
S. A. Robertson, T. Graves, J. J. Biafore, M. D. Smith, KLA-Tencor (United States)

SESSION 7 TOOLS RELATED PROCESS CONTROL I

- 7274 0Q **Scanner OPC signatures: automatic vendor-to-vendor OPE matching** [7274-86]
S. P. Renwick, Nikon Precision, Inc. (United States)
- 7274 OR **Dense lines created by spacer DPT scheme: process control by local dose adjustment using advanced scanner control** [7274-26]
J. Finders, ASML (Netherlands); M. Dusa, ASML US, Inc. (United States); B. Vleeming, T. Fliervoet, B. Hepp, H. Megens, R. Groenendijk, J. Quaedackers, E. Mos, C. Leewis, F. Bornebroek, ASML (Netherlands); M. Maenhoudt, M. Leblans, T. Vandeweyer, G. Murdoch, E. Altamirano Sanchez, IMEC vzw (Belgium)
- 7274 OS **Focus and dose characterization of immersion photoclusters** [7274-27]
T. A. Brunner, D. Corliss, T. Wiltshire, C. P. Ausschnitt, IBM SRDC (United States)
- 7274 OT **Model-based scanner tuning in a manufacturing environment** [7274-114]
C. Y. Shih, R. C. Peng, T. C. Chien, Y. W. Guo, J. Y. Lee, C. L. Chang, P. C. Huang, H. H. Liu, H. J. Lee, J. Lin, K. W. Chang, C. P. Yeh, Taiwan Semiconductor Manufacturing Co. (Taiwan); W. J. Shao, H. Cao, A. Bruguier, X. Xie, C. H. Chang, R. Aldana, Y. Cao, R. Goossens, Brion Technologies Inc., ASML(United States); S. Hsieh, ASML (Netherlands)
- 7274 OU **Scanner-dependent optical proximity effects** [7274-29]
J. K. Tyminski, Nikon Precision, Inc. (United States); T. Matsuyama, T. Nakashima, R. Inoue, Nikon Corp. (Japan)

SESSION 8 TOOLS RELATED PROCESS CONTROL II

- 7274 0V **Challenges and solutions in the calibration of projection lens pupil-image metrology tools** [7274-30]
S. Slonaker, B. Riffel, Nikon Precision, Inc. (United States); H. Nishinaga, Nikon Corp. (Japan)
- 7274 0W **Impact of CD and overlay errors on double-patterning processes** [7274-31]
C. Lapeyre, S. Barnola, I. Servin, S. Gaugirana, CEA/LETI-Minatec (France); V. Salvetat, Nikon Precision Europe GmbH (France); N. Magome, A. J. Hazelton, Nikon Corp. (Japan); M. McCallum, Nikon Precision Europe GmbH (United Kingdom)
- 7274 0X **Achieving overlay budgets for double patterning** [7274-32]
A. J. Hazelton, N. Magome, S. Wakamoto, A. Tokui, Nikon Corp. (Japan); C. Lapeyre, S. Barnola, G. Jullien, CEA/LETI-Minatec (France); V. Salvetat, Nikon Precision Europe GmbH (Germany)
- 7274 0Y **Innovative pattern matching method considering process margin and scanner design information** [7274-33]
K. Tsujita, K. Mikami, H. Ishii, R. Nakayama, M. Arakawa, T. Ueno, S. Fujie, K. Takahashi, Canon, Inc. (Japan)

SESSION 9 OPTICAL PROXIMITY CORRECTIONS I

- 7274 0Z **A new method for post-etch OPC modeling to compensate for underlayer effects from integrated wafers** [7274-34]
C. Sarma, Infineon Technologies NA (United States); A. Abdo, D. Dunn, D. Fischer, IBM Microelectronics (United States); K. Herold, Infineon Technologies NA (United States); S. Mansfield, L. Tsou, IBM Microelectronics (United States)
- 7274 10 **Optimal setting strategy for kernel-based OPC simulation engines** [7274-35]
K. Kodera, S. Tanaka, T. Kotani, S. Inoue, Toshiba Corp. Semiconductor Co. (Japan)
- 7274 11 **Improving yield through the application of process window OPC** [7274-36]
J. Tirapu Azpiroz, A. Krasnoperova, S. Siddiqui, K. Settlemyer, I. Graur, I. Stobert, J. M. Oberschmidt, IBM Microelectronics (United States)
- 7274 12 **Etch aware optical proximity correction: a first step toward integrated pattern engineering** [7274-37]
D. N. Dunn, S. Mansfield, I. Stobert, IBM (United States); C. Sarma, Infineon Technologies (United States); G. Lembach, Advanced Micro Devices (United States); J. Liu, Chartered Semiconductor (United States); K. Herold, Infineon Technologies (United States)
- 7274 13 **Integrating assist feature print fixing with OPC** [7274-38]
L. D. Barnes, A. Poonawala, B. D. Painter, A. M. Jost, T. Takei, Y. Li, Synopsys, Inc. (United States)
- 7274 14 **Double-patterning-friendly OPC** [7274-39]
X. Li, G. Luk-Pat, Synopsys, Inc. (United States); C. Cork, Synopsys, Inc. (France); L. Barnes, K. Lucas, Synopsys, Inc. (United States)

SESSION 10 OPTICAL PROXIMITY CORRECTIONS II

- 7274 15 **Calibrating OPC model with full CD profile data for 2D and 3D patterns using scatterometry** [7274-40]
A. D. Dave, Mentor Graphics Corp. (United States); O. Kritsun, Y. Deng, K. Yoshimoto, GLOBALFOUNDRIES (United States); J. Li, J. Hu, Nanometrics, Inc. (United States)
- 7274 16 **Impact of modelisation pixel size on OPC consistency** [7274-41]
F. Foussadier, E. Yesilada, J.-C. Le Denmat, STMicroelectronics (France); Y. Trouiller, CEA/Leti (France); V. Farys, F. Robert, G. Kerrien, C. Gardin, STMicroelectronics (France); L. Perraud, CEA/Leti (France); F. Vautrin, A. Villaret, C. Martinelli, J. Planchot, STMicroelectronics (France); J. L. Di-Maria, CEA/Leti (France); M. Saied, M. K. Top, STMicroelectronics (France)
- 7274 17 **OPC simplification and mask cost reduction using regular design fabrics** [7274-42]
T. Jhaveri, Carnegie Mellon Univ. (United States) and PDF Solutions (United States); I. Stobert, L. Liebmann, IBM Microelectronics (United States); P. Karakatsanis, PDF Solutions (Germany); V. Rovner, A. Strojwas, L. Pileggi, Carnegie Mellon Univ. (United States) and PDF Solutions (United States)
- 7274 18 **Resist development modeling for OPC accuracy improvement** [7274-43]
Y. Fan, L. Zavyalova, Y. Zhang, C. Zhang, K. Lucas, B. Falch, E. Croffie, J. Li, L. Melvin, B. Ward, Synopsys, Inc. (United States)

SESSION 11 OPTICAL PROXIMITY CORRECTIONS III

7274 19 **OPC for reduced process sensitivity in the double patterning flow** [7274-44]

M. Gheith, L. Hong, J. Word, Mentor Graphics Corp. (United States)

7274 1A **Through-focus pattern matching applied to double patterning** [7274-45]

J. Rubinstein, A. R. Neureuther, Univ. of California, Berkeley (United States)

SESSION 12 RESOLUTION ENHANCEMENT

7274 1B **A novel methodology for hybrid mask AF generation for 22 and 15nm technology** [7274-46]

Y. Zou, L. Capodieci, C. Tabery, Advanced Micro Devices (United States)

7274 1C **Pushing the limits of RET with different illumination optimization methods** [7274-129]

A. D. Dave, Mentor Graphics Corp. (United States); R. Kim, Advanced Micro Devices, Inc. (United States)

7274 1E **A computational technique to optimally design in-situ diffractive elements: applications to projection lithography at the resist resolution limit** [7274-50]

G. R. Feijoo, Woods Hole Oceanographic Institution (United States); J. Tirapu-Azpiroz, IBM SRDC Microelectronics (United States); A. E. Rosenbluth, IBM Thomas J. Watson Research Ctr. (United States); A. A. Oberai, J. J. Mohan, Rensselaer Polytechnic Institute (United States); K. Tian, IBM SRDC Microelectronics, (United States); D. Melville, D. Gil, IBM Thomas J. Watson Research Ctr. (United States); K. Lai, IBM SRDC Microelectronics (United States)

7274 1F **Feasibility of ultra-low k_1 lithography for 28nm CMOS node** [7274-51]

S. Mimotogi, K. Takahata, Toshiba Corp. Semiconductor Co. (Japan); T. Murakami, S. Nagahara, K. Takeda, NEC Electronics Corp. (Japan); M. Satake, Y. Kitamura, T. Ojima, H. Fujise, Y. Seino, T. Ema, H. Yonemitsu, M. Takakuwa, S. Nakagawa, T. Kono, M. Asano, S. Kyoh, H. Harakawa, A. Nomachi, T. Ishida, S. Hasegawa, K. Miyashita, Toshiba Corp. Semiconductor Co. (Japan); M. Tominaga, NEC Electronics Corp. (Japan); S. Inoue, Toshiba Corp. Semiconductor Co. (Japan)

SESSION 13 PROCESS

7274 1G **Defectivity improvement by modified wafer edge treatment in immersion lithography** [7274-103]

M. Fujita, T. Tamura, N. Onoda, T. Uchiyama, NEC Electronics Corp. (Japan)

7274 1H **Design of resist stacks with antireflection coatings from the viewpoint of focus budget** [7274-53]

S. Nagai, K. Sato, Toshiba Corp. Semiconductor Co. (Japan)

SESSION 14 TOOLS I

7274 1I **An innovative platform for high-throughput high-accuracy lithography using a single wafer stage** [7274-54]

Y. Shibasaki, H. Kohno, M. Hamatani, Nikon Corp. (Japan)

- 7274 1J **Novel approaches to meet the requirements for double patterning** [7274-55]
T. Ebihara, T. Yoshihara, H. Morohoshi, T. Makiyama, Y. Kawanobe, K. Tsujita, T. Kojima, K. Takahashi, Canon, Inc. (Japan)
- 7274 1K **Extending single-exposure patterning towards 38-nm half-pitch using 1.35 NA immersion** [7274-56]
I. Bouchoms, A. Engelen, J. Mulkens, H. Boom, R. Moerman, P. Liebregts, R. de Graaf, M. van Veen, P. Thomassen, ASML Netherlands B.V. (Netherlands); W. Emer, Carl Zeiss SMT AG (Germany); F. Sperling, ASML Netherlands B.V. (Netherlands)
- 7274 1L **Advanced aberration control in projection optics for double patterning** [7274-57]
T. Yoshihara, T. Sukegawa, N. Yabu, M. Kobayashi, T. Arai, T. Kitamura, A. Shigenobu, Y. Hasegawa, K. Takahashi, Canon, Inc. (Japan)
- 7274 1M **Polarization aberration control for ArF projection lenses** [7274-58]
T. Matsuyama, N. Kita, Nikon Corp. (Japan)

SESSION 15 TOOLS II

- 7274 1O **Modeling laser bandwidth for OPC applications** [7274-60]
C. Zuniga, K. Adam, M. Lam, Mentor Graphics Corp. (United States); I. Lalovic, Cymer, Inc. (United States); P. De Bisschop, IMEC (Belgium)
- 7274 1P **Control and reduction of immersion defectivity for yield enhancement at high volume production** [7274-61]
K. Nakano, R. Seki, T. Sekito, M. Yoshida, T. Fujiwara, Y. Iriuchijima, S. Owa, Nikon Corp. (Japan)
- 7274 1Q **Imaging solutions for the 22nm node using 1.35NA** [7274-62]
A. Engelen, M. Mulder, I. Bouchoms, ASML (Netherlands); S. Hansen, ASML US, Inc. (United States); A. Bouma, A. Ngai, M. van Veen, ASML (Netherlands); J. Zimmermann, Carl Zeiss SMT AG (Germany)
- 7274 1R **Speckle in optical lithography and the influence on line width roughness** [7274-63]
O. Noordman, A. Tychkov, J. Baselmans, ASML Netherlands B.V. (Netherlands); J. Tsacoyeanes, G. Politi, ASML Wilton (United States); M. Patra, V. Blahnik, M. Maul, Carl Zeiss SMT AG (Germany)
- 7274 1S **Enabling the lithography roadmap: an immersion tool based on a novel stage positioning system** [7274-64]
F. de Jong, B. van der Pasch, T. Castenmiller, B. Vleeming, R. Droste, F. van de Mast, ASML Netherlands B.V. (Netherlands)

Part Two

POSTER SESSION: DOUBLE PATTERNING

- 7274 1U **A CDU comparison of double patterning process options using Monte Carlo simulation** [7274-66]
J. Hooge, Tokyo Electron America (United States); S. Hatakeyama, K. Nafus, Tokyo Electron Kyushu, Ltd. (Japan); S. Scheer, Tokyo Electron America (United States); P. Foubert, S. Cheng, P. Leray, IMEC (Belgium)
- 7274 1V **Exploration of linear and non-linear double exposure techniques by simulation** [7274-67]
J. S. Petersen, R. T. Greenway, Petersen Advanced Lithography, Inc. (United States); T. Fühner, P. Evanschitzky, F. Shao, A. Erdmann, Fraunhofer Institute of Integrated Systems and Device Technology (Germany)
- 7274 1X **Integration of dry etching steps for double patterning and spacer patterning processes** [7274-69]
S. Barnola, C. Lapeyre, I. Servin, C. Arvet, P. Maury, L. Mage, CEA/LETI-Minatec (France)
- 7274 1Y **Analysis of higher order pitch division for sub-32nm lithography** [7274-70]
P. Xie, B. W. Smith, Rochester Institute of Technology (United States)

POSTER SESSION: HIGH INDEX LITHOGRAPHY

- 7274 1Z **32 nm half pitch formation with high numerical aperture single exposure** [7274-71]
M. Jung, J.-M. Park, Hanyang Univ. (Korea, Republic of); M. Kim, S. Hong, J. Kim, Seoul National Univ. (Korea, Republic of); I.-H. Park, Univ. of Incheon (Korea, Republic of); H.-K. Oh, Hanyang Univ. (Korea, Republic of)
- 7274 20 **High index 193 nm immersion lithography: the beginning or the end of the road** [7274-72]
P. A. Zimmerman, B. J. Rice, Intel Corp. (United States) and SEMATECH Inc. (United States); E. C. Piscani, SEMATECH Inc. (United States); V. Liberman, MIT Lincoln Lab. (United States)
- 7274 21 **Birefringence issues with uniaxial crystals as last lens elements for high-index immersion lithography** [7274-73]
J. H. Burnett, E. C. Benck, S. G. Kaplan, National Institute of Standards and Technology (United States); G. Y. Sirat, Crystalith (Israel); C. Mack, Crystalith (United States)

POSTER SESSION: MASKS

- 7274 22 **Multiple layer CD control treatment** [7274-76]
A. Birnstein, C. Röpke, M. Sczyrba, AMTC GmbH & Co. KG (Germany); R. Pforr, M. Hennig, Qimonda Dresden GmbH & Co. OHG (Germany); G. Ben-Zvi, E. Graitzer, A. Cohen, Pixer Technology Ltd. (Israel)
- 7274 23 **Smart data filtering for enhancement of model accuracy** [7274-77]
S. Abdelwahed, Mentor Graphics Corp. (Egypt); J. H. Kang, J. Choi, J. D. Kim, H. Lee, S. Jun, Y. Kim, Dongbu HiTek Co., Ltd. (Korea, Republic of)

- 7274 24 **Analysis and modeling of photomask edge effects for 3D geometries and the effect on process window** [7274-78]
M. A. Miller, A. R. Neureuther, Univ. of California, Berkeley (United States)

POSTER SESSION: OPTICAL PROXIMITY CORRECTIONS

- 7274 25 **Transformation procedure from sparse OPC model to grid-based model** [7274-79]
Q. Liu, Semiconductor Manufacturing International Corp. (China); L. Zhang, Mentor Graphics Corp. (China)
- 7274 26 **Image-assistant OPC model calibration on 65nm node contact layer** [7274-80]
Y. Y. Tsai, S. L. Tsai, F. Lo, E. Yang, T. H. Yang, K. C. Chen, C.-Y. Lu, Macronix International Co., Ltd. (Taiwan)
- 7274 27 **Design driven test patterns for OPC models calibration** [7274-82]
M. Al-Imam, Mentor Graphics Corp. (Egypt)
- 7274 28 **Model-based retarget for 45nm node and beyond** [7274-85]
E. Yang, C. H. Li, Semiconductor Manufacturing International Corp. (China); X. H. Kang, Mentor Graphics Corp. (China); E. Guo, Semiconductor Manufacturing International Corp. (China)
- 7274 29 **Pattern matching assisted modeling test pattern generation** [7274-87]
L. Hong, Q. Li, J. Rao, Mentor Graphics Corp. (United States)
- 7274 2A **Model based mask process correction and verification for advanced process nodes** [7274-89]
T. Lin, T. Donnelly, S. Schulze, Mentor Graphics Corp. (United States)
- 7274 2C **Novel OPC method to create sub 45nm contact hole using design based metrology** [7274-91]
D.-J. Lee, S. Oh, J. Park, J. Choi, J. Kim, C. Kim, D. Yim, Hynix Semiconductor, Inc. (Korea, Republic of)
- 7274 2D **Abbe-PCA (Abbe-Hopkins): microlithography aerial image analytical compact kernel generation based on principle component analysis** [7274-92]
M.-F. Tsai, S.-J. Chang, C. C. P. Chen, National Taiwan Univ. (Taiwan); L. S. Melvin III, Synopsys, Inc. (United States)
- 7274 2F **Automatic SRAF size optimization during OPC** [7274-98]
S. Jayaram, J. Word, Mentor Graphics Corp. (United States)
- 7274 2G **OPC segmentation: dilemma between degree-of-freedom and stability with some relieves** [7274-99]
Y. P. Tang, J. H. Feng, M. H. Chih, C. K. Tsai, W. C. Huang, C. C. Kuo, R. G. Liu, H. T. Lin, Y. C. Ku, Taiwan Semiconductor Manufacturing Co. (Taiwan)
- 7274 2H **Efficient hardware usage in the mask tapeout flow** [7274-100]
M. Boman, T. Brist, Y. Wang, Synopsys, Inc. (United States)

- 7274 2I **Pre-OPC layout decomposition for improved image fidelity** [7274-101]
S. Abdelwahed, Mentor Graphics Corp. (Egypt); R. Fathy, Mentor Graphics Corp. (United States); J. H. Kang, J. D. Kim, Y. Kim, Dongbu HiTek Co., Ltd. (Korea, Republic of)

POSTER SESSION: PROCESS

- 7274 2J **Next generation siloxane-based Bottom Anti-Reflective Coating (BARC) formulations with selective strip rates and required optical properties** [7274-102]
S. Mukhopadhyay, J. Kennedy, Y. Pandey, P. Amin, J. Gill, Honeywell Electronic Materials (United States)
- 7274 2K **Thin hardmask patterning stacks for the 22-nm node** [7274-104]
Z. Zhu, Brewer Science, Inc. (United States); E. Piscani, SEMATECH Inc. (United States); Y. Wang, J. Macie, C. J. Neef, B. Smith, Brewer Science, Inc. (United States)
- 7274 2L **Arbitrary three-dimensional micro-fabrication by polymer grayscale lithography** [7274-105]
L. Jiang, P. Nath, Tuskegee Univ. (United States); N. S. Korivi, Louisiana State Univ. (United States)
- 7274 2N **0.13µm BiCMOS emitter window lithography with KrF scanners** [7274-107]
L.-H. Chou, N. S. Patel, P. M. McCarthy, National Semiconductor Corp. (United States)
- 7274 2O **Patterning of SU-8 resist with digital micromirror device (DMD) maskless lithography** [7274-109]
T. Wang, Univ. of Wisconsin, Madison (United States); M. Quaglio, F. Pirri, Polytechnic of Torino (Italy); Y.-C. Cheng, D. Busacker, Univ. of Wisconsin, Madison (United States); F. Cerrina, Univ. of Wisconsin, Madison (United States) and Univ. of Boston (United States)

POSTER SESSION: PROCESS CONTROL

- 7274 2P **Process transfer strategies between ASML immersion scanners** [7274-113]
Y. He, Micron Technology, Inc. (United States); P. Engblom, ASML (United States); J. Zhou, Micron Technology, Inc. (United States); E. Janda, ASML (United States); A. Devilliers, Micron Technology, Inc. (United States); B. Geh, Carl Zeiss SMT AG (Germany); E. Byers, Micron Technology, Inc. (United States); J. Menger, Carl Zeiss SMT AG (Germany); S. Hansen, M. Dusa, ASML (United States)
- 7274 2Q **32nm node device laser-bandwidth OPE sensitivity and process matching** [7274-115]
K. Yoshimochi, T. Tamura, T. Kurabayashi, T. Uchiyama, NEC Electronics Corp. (Japan); N. Farrar, T. Oga, Cymer, Inc. (United States); J. Bonafede, Cymer Japan, Inc. (Japan)
- 7274 2S **New approach to determine best beam focus** [7274-117]
C. Zuniga, T. M. Tawfik, Mentor Graphics Corp. (United States)
- 7274 2T **High-order distortion effects induced by extreme off-axis illuminations at hyper NA lithography** [7274-118]
P. Rigolli, G. Capetti, E. De Chiara, Numonyx (Italy); L. Amato, STMicroelectronics (Italy); U. Iessi, P. Canestrari, Numonyx (Italy); C. Llorens, ASML Rousset (France); S. Smit, ASML Netherlands B.V. (Netherlands); L. Brige, ASML Rousset (France); J. Plauth, ASML Italy srl (Italy)

POSTER SESSION: RESOLUTION ENHANCEMENT

- 7274 2V **Line end shortening and corner rounding for novel off-axis illumination source shapes** [7274-124]
M. L. Ling, National Univ. of Singapore (Singapore); G. S. Chua, Q. Lin, Chartered Semiconductor Manufacturing, Ltd. (Singapore); C. J. Tay, C. Quan, National Univ. of Singapore (Singapore)
- 7274 2W **The analysis of polarization characteristics on 40nm memory devices** [7274-125]
M. Yoo, C. Park, T. You, H. Yang, Hynix Semiconductor, Inc. (Korea, Republic of); Y.-H. Min, K.-Y. Park, ASML Korea (Korea, Republic of); D. Yim, S. Park, Hynix Semiconductor, Inc. (Korea, Republic of)
- 7274 2X **22 nm technology node active layer patterning for planar transistor devices** [7274-126]
R. Kim, Advanced Micro Devices, Inc. (United States); S. Holmes, S. Halle, IBM Research (United States); V. Dai, Advanced Micro Devices, Inc. (United States); J. Meiring, IBM SRDC (United States); A. Dave, Mentor Graphics Corp. (United States); M. E. Colburn, IBM Research (United States); H. J. Levinson, Advanced Micro Devices, Inc. (United States)
- 7274 2Y **C-quad polarized illumination for back end thin wire: moving beyond annular illumination regime** [7274-128]
S. S. Mehta, Chartered Semiconductor Manufacturing, Ltd. (United States); H.-R. Lee, SAMSUNG Electronics Co., Ltd. (United States); B. Hamieh, STMicroelectronics N.V. (United States); C. Kallinal, I. Matthew, Advanced Micro Devices, Inc. (United States); R. Viswanathan, D. N. Dunn, IBM Semiconductor Research and Development Ctr. (United States)

POSTER SESSION: SIMULATION

- 7274 2Z **A proposed image intensity expressing local irradiance** [7274-131]
S. Nakao, I. Kanai, S. Maejima, M. Okuno, N. Tamada, J. Sakai, A. Imai, T. Hanawa, K. Sukou, Renesas Technology (Japan)
- 7274 30 **The divergence of image and resist process metrics** [7274-132]
J. J. Biafore, S. Kapasi, S. A. Robertson, M. D. Smith, KLA-Tencor (United States)
- 7274 31 **Advanced model and fast algorithm for aerial image computation with well controlled accuracy** [7274-133]
V. Manuylov, Robust Chip Inc. (United States)
- 7274 32 **A novel fast 3D resist simulation method using Chebyshev expansion** [7274-134]
M. Takahashi, S. Tanaka, S. Mimotogi, S. Inoue, Toshiba Corp. Semiconductor Co. (Japan)
- 7274 33 **Modeling mask scattered field at oblique incidence (Best Student Paper Award)** [7274-135]
T. M. Tawfik, Mentor Graphics Corp. (Egypt); A. H. Morshed, D. Khalil, Ain Shams Univ. (Egypt)
- 7274 34 **Partially coherent image computation using elementary functions** [7274-136]
A. Smith, A. Burvall, C. Dainty, National Univ. of Ireland, Galway (Ireland)

- 7274 35 **Chemically amplified resist modeling in OPC** [7274-137]
X. Zheng, J. Huang, Synopsys, Inc. (United States); F. Kuo, Synopsys, Inc. (Taiwan); A. Kazarian, F. Chin, Y. Fan, Synopsys, Inc. (United States)
- 7274 36 **High-speed microlithography aerial image contour generation without images** [7274-138]
S. Lin, C. C. P. Chen, National Taiwan Univ. (Taiwan); L. S. Melvin III, Synopsys, Inc. (United States)

POSTER SESSION: SOURCE AND MASK OPTIMIZATION

- 7274 37 **PSM design for inverse lithography with partially coherent illumination** [7274-139]
X. Ma, G. R. Arce, Univ. of Delaware (United States)
- 7274 39 **Manufacturability of ILT patterns in low-NA 193nm environment** [7274-141]
C. Lim, V. Temchenko, I. Meusel, D. Kaiser, J. Schneider, Infineon Technologies Dresden GmbH and Co. OHG (Germany); M. Niehoff, Mentor Graphics Corp. (Germany)
- 7274 3A **Inverse vs. traditional OPC for the 22nm node** [7274-142]
J. Word, Y. Granik, M. Medvedeva, S. Rodin, Mentor Graphics Corp. (United States); L. Capodieci, Y. Deng, J. Kye, C. Tabery, K. Yoshimoto, Y. Zou, Advanced Micro Devices (United States); H. Diab, Mentor Graphics Corp. (Egypt); M. Gheith, Mentor Graphics Corp. (United States); M. Habib, Mentor Graphics Corp. (Egypt); C. Zhu, Mentor Graphics Corp. (United States)
- 7274 3B **Innovative pixel-inversion calculation for model-based sub-resolution assist features and optical proximity correction** [7274-143]
J.-C. Yu, P. Yu, H.-Y. Chao, National Chiao-Tung Univ. (Taiwan)
- 7274 3D **Source optimization for three-dimensional image designs through film stacks** [7274-145]
D. O. S. Melville, A. E. Rosenbluth, IBM Thomas J. Watson Research Ctr. (United States); K. Tian, IBM Semiconductor Research and Development Ctr. (United States); D. Goldfarb, IBM Thomas J. Watson Research Ctr. (United States); S. Harrer, M. Colburn, IBM Research at Albany NanoTech (United States)

POSTER SESSION: SPACER-BASED PROCESSES

- 7274 3E **Pattern decomposition and process integration of self-aligned double patterning for 30nm node NAND FLASH process and beyond** [7274-147]
Y.-S. Chang, M.-F. Tsai, C.-C. Lin, J.-C. Lai, Powerchip Semiconductor Corp. (Taiwan)
- 7274 3F **A manufacturing lithographic approach for high density MRAM device using KrF double mask patterning technique** [7274-146]
D. Liu, T. Zhong, T. Tornq, Magic Technologies (United States)
- 7274 3G **Alignment and overlay improvements for 3x nm and beyond process with CVD sidewall spacer double patterning** [7274-148]
H. Dai, C. Bencher, Y. Chen, S. Sun, X. Xu, C. Ngai, Applied Materials, Inc. (United States)

POSTER SESSION: TOOLS

- 7274 3H **Birefringence simulations of annealed ingot of calcium fluoride single crystal: consideration of creep behavior of ingot during annealing process** [7274-151]
N. Miyazaki, H. Ogino, Y. Kitamura, Kyoto Univ. (Japan); T. Mabuchi, T. Nawata, Tokuyama Corp. (Japan)
- 7274 3I **Cost-effective shrink of semi-critical layers using the TWINSCAN XT:1000H NA 0.93 Kr scanner** [7274-152]
F. Bornebroek, M. de Wit, W. de Boeij, G. Dicker, ASML (Netherlands); J. Hong, ASML (Taiwan); A. Serebryakov, ASML (Netherlands)
- 7274 3J **Optical performance of laser light source for ArF immersion double patterning lithography tool** [7274-153]
K. Wakana, H. Tsushima, S. Matsumoto, M. Yoshino, T. Kumazaki, H. Watanabe, T. Ohta, S. Tanaka, T. Suzuki, H. Nakarai, Y. Kawasaji, A. Kurosu, T. Matsunaga, J. Fujimoto, H. Mizoguchi, Gigaphoton Inc. (Japan)
- 7274 3K **True polarization characteristics of hyper-NA optics excluding impact of measurement system** [7274-155]
T. Fujii, K. Muramatsu, Nikon Corp. (Japan); N. Matsuo, Nikon Systems, Inc. (Japan); Y. Ohmura, Nikon Corp. (Japan); M. Sawada, Nikon Systems, Inc. (Japan)
- 7274 3L **Reliability report of high power injection lock laser light source for double exposure and double patterning ArF immersion lithography** [7274-156]
H. Tsushima, M. Yoshino, T. Ohta, T. Kumazaki, H. Watanabe, S. Matsumoto, H. Nakarai, H. Umeda, Y. Kawasaji, T. Suzuki, S. Tanaka, A. Kurosu, T. Matsunaga, J. Fujimoto, H. Mizoguchi, Gigaphoton Inc. (Japan)
- 7274 3M **Immersion-cluster uptime enhancement technology toward high-volume manufacturing** [7274-157]
R. Tanaka, T. Fujiwara, K. Nakano, Nikon Corp. (Japan); S. Wakamizu, H. Kyouda, Tokyo Electron Kyushu, Ltd. (Japan)
- 7274 3N **Lithography line productivity impact using Cymer GLX technology** [7274-158]
K. O'Brien, W. J. Dunstan, R. Jacques, D. Brown, Cymer, Inc. (United States)
- 7274 3O **Enabling high volume manufacturing of double patterning immersion lithography with the XLR 600ix ArF light source** [7274-159]
R. Rokitski, V. Fleurov, R. Bergstedt, H. Ye, R. Rafac, R. Jacques, F. Trintchouk, T. Ishihara, R. Rao, T. Cacouris, D. Brown, W. Partlo, Cymer, Inc. (United States)

Author Index